

MJE15032 (NPN), MJE15033 (PNP)

Complementary Silicon Plastic Power Transistors

Designed for use as high-frequency drivers in audio amplifiers.

Features

- High DC Current Gain
- High Current Gain – Bandwidth Product
- TO-220 Compact Package
- Epoxy Meets UL 94 V-0 @ 0.125 in
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CE0}	250	Vdc
Collector-Base Voltage	V_{CB}	250	Vdc
Emitter-Base Voltage	V_{EB}	5.0	Vdc
Collector Current – Continuous	I_C	8.0	Adc
Collector Current – Peak	I_{CM}	16	Adc
Base Current	I_B	2.0	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	50 0.40	W W/ $^\circ\text{C}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	2.0 0.016	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
ESD – Human Body Model	HBM	3B	V
ESD – Machine Model	MM	C	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.5	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

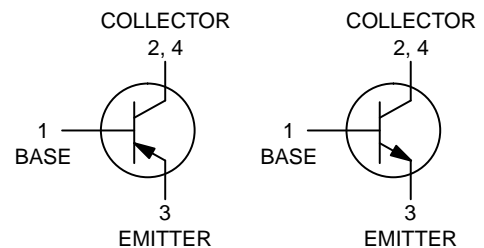


ON Semiconductor®

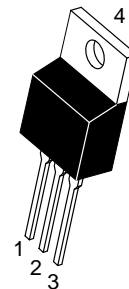
<http://onsemi.com>

8.0 AMPERES POWER TRANSISTORS COMPLEMENTARY SILICON 250 VOLTS, 50 WATTS

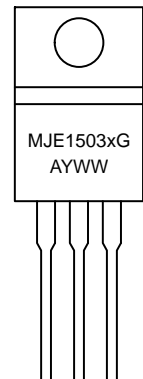
COMPLEMENTARY



MARKING DIAGRAM



**TO-220
CASE 221A
STYLE 1**



MJE1503x = Specific Device Code
 x = 2 or 3
 A = Assembly Location
 Y = Year
 WW = Work Week
 G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
MJE15032G	TO-220 (Pb-Free)	50 Units/Rail
MJE15033G	TO-220 (Pb-Free)	50 Units/Rail

MJE15032 (NPN), MJE15033 (PNP)

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (Note 1) ($I_C = 10\text{ mA}$, $I_B = 0$)	$V_{CEO(sus)}$	250	–	Vdc
Collector Cutoff Current ($V_{CB} = 250\text{ Vdc}$, $I_E = 0$)	I_{CBO}	–	10	μA
Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	10	μA
ON CHARACTERISTICS (Note 1)				
DC Current Gain ($I_C = 0.5\text{ A}$, $V_{CE} = 5.0\text{ Vdc}$) ($I_C = 1.0\text{ A}$, $V_{CE} = 5.0\text{ Vdc}$) ($I_C = 2.0\text{ A}$, $V_{CE} = 5.0\text{ Vdc}$)	h_{FE}	70 50 10	– – –	–
Collector–Emitter Saturation Voltage ($I_C = 1.0\text{ A}$, $I_B = 0.1\text{ A}$)	$V_{CE(sat)}$	–	0.5	Vdc
Base–Emitter On Voltage ($I_C = 1.0\text{ A}$, $V_{CE} = 5.0\text{ Vdc}$)	$V_{BE(on)}$	–	1.0	Vdc
DYNAMIC CHARACTERISTICS				
Current Gain – Bandwidth Product (Note 2) ($I_C = 500\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f_{test} = 1.0\text{ MHz}$)	f_T	30	–	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.
2. $f_T = |h_{fe}| \cdot f_{test}$.

MJE15032 (NPN), MJE15033 (PNP)



Figure 1. Thermal Response

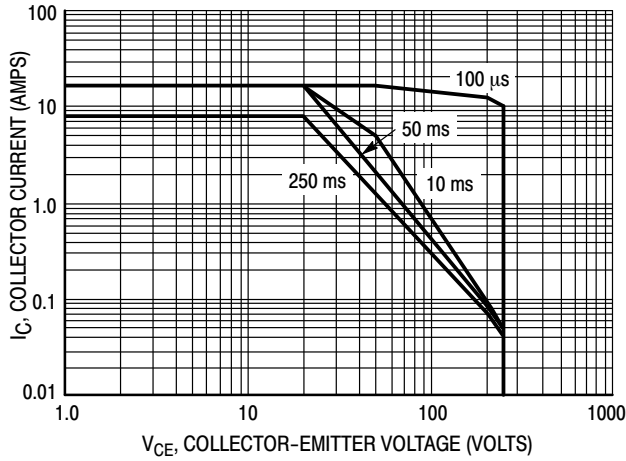


Figure 2. MJE15032 & MJE15033 Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 2 and 4 is based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} < 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 1. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

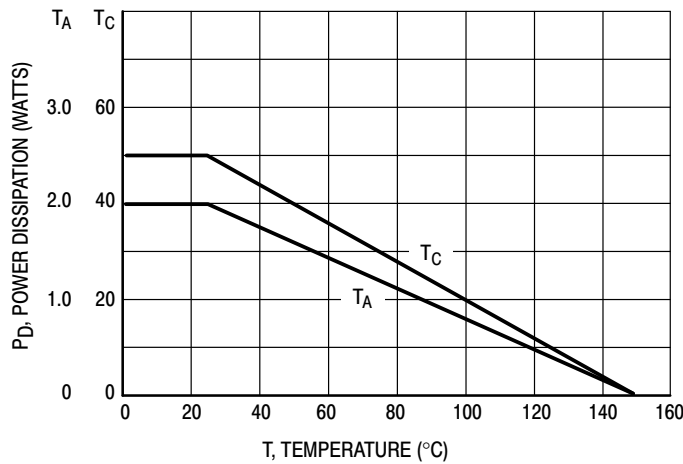


Figure 3. Power Derating

MJE15032 (NPN), MJE15033 (PNP)

NPN – MJE15032

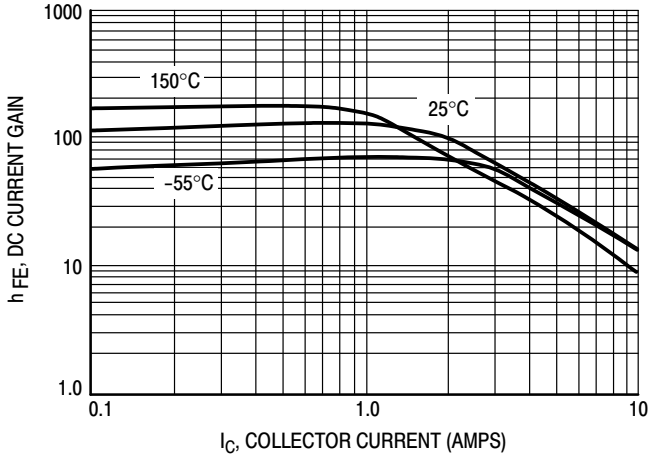


Figure 4. NPN – MJE15032
 $V_{CE} = 5\text{ V}$ DC Current Gain

PNP – MJE15033

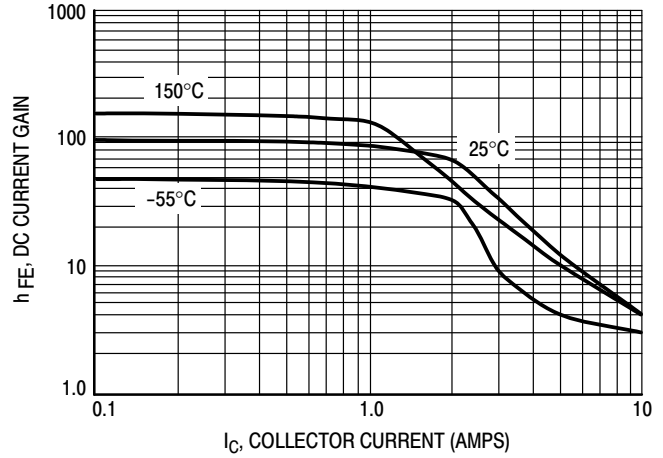


Figure 5. PNP – MJE15033
 $V_{CE} = 5\text{ V}$ DC Current Gain

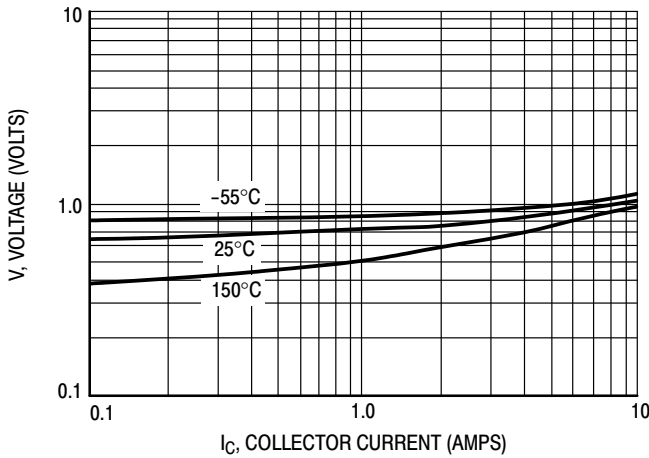


Figure 6. NPN – MJE15032
 $V_{CE} = 5\text{ V}$ $V_{BE(on)}$ Curve



Figure 7. PNP – MJE15033
 $V_{CE} = 5\text{ V}$ $V_{BE(on)}$ Curve

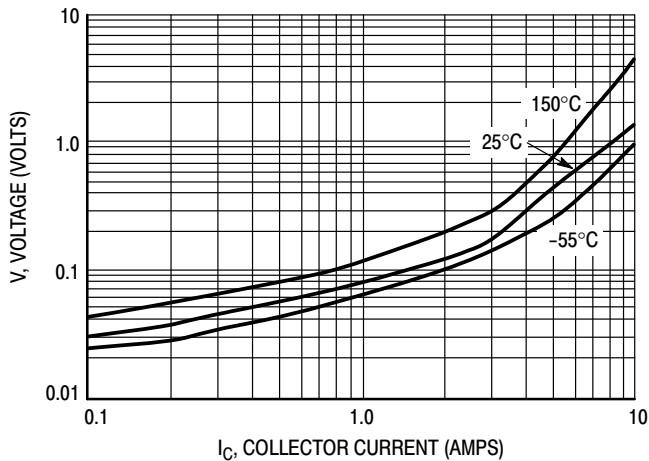


Figure 8. NPN – MJE15032
 $V_{CE(sat)}$ $I_C/I_B = 10$

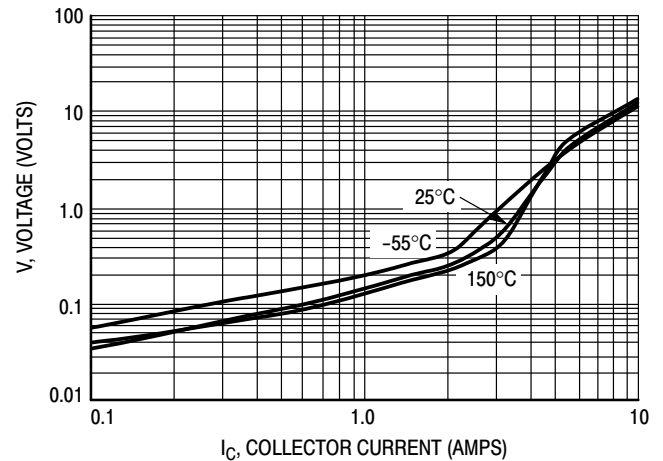


Figure 9. PNP – MJE15033
 $V_{CE(sat)}$ $I_C/I_B = 10$

MJE15032 (NPN), MJE15033 (PNP)

NPN – MJE15032

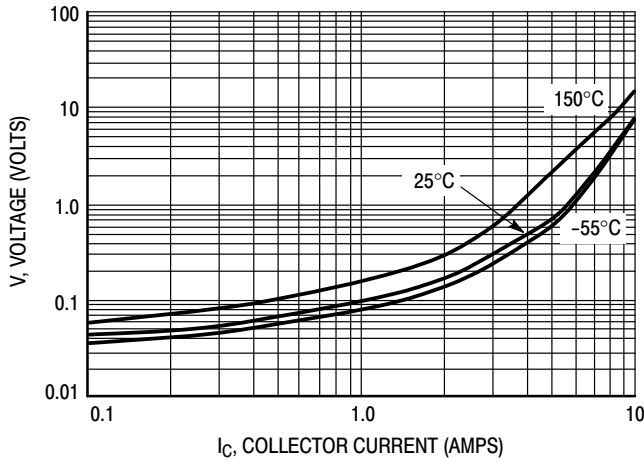


Figure 10. NPN – MJE15032
 $V_{CE(sat)} I_C/I_B = 20$

PNP – MJE15033



Figure 11. PNP – MJE15033
 $V_{CE(sat)} I_C/I_B = 20$

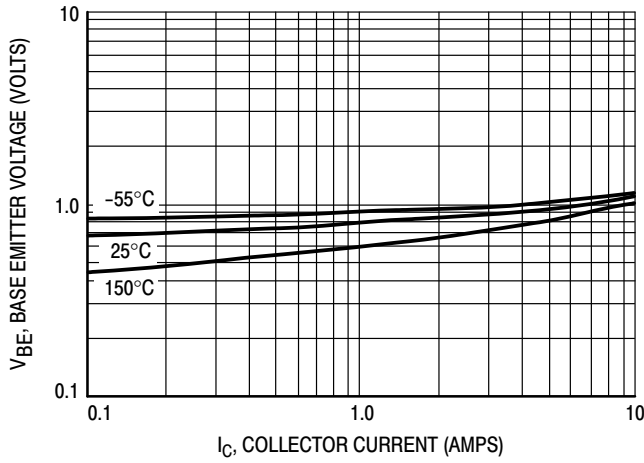


Figure 12. NPN – MJE15032
 $V_{BE(sat)} I_C/I_B = 10$

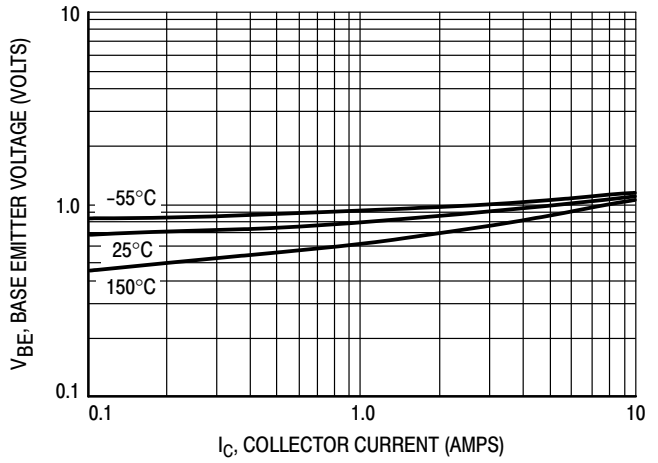
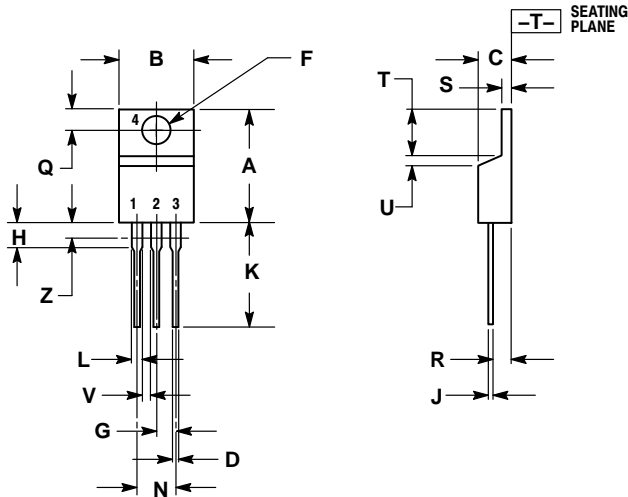


Figure 13. PNP – MJE15033
 $V_{BE(sat)} I_C/I_B = 10$

MJE15032 (NPN), MJE15033 (PNP)

PACKAGE DIMENSIONS

TO-220
CASE 221A-09
ISSUE AH



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 1:

1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>
For additional information, please contact your local Sales Representative